



**isc Silicon PNP Power Transistor****2SB891****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -50 \mu\text{A}; I_E = 0$	-40			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; I_B = 0$	-32			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -50 \mu\text{A}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-0.8	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -20\text{V}; I_E = 0$			-1.0	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-1.0	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -3\text{V}$	82		390	

◆  **$h_{FE}$  Classifications**

P	Q	R
82-180	120-270	180-390

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